On the Way to Twisted Bilayer Graphene: Formation and Decoupling of 0°-Rotated Epitaxial Graphene



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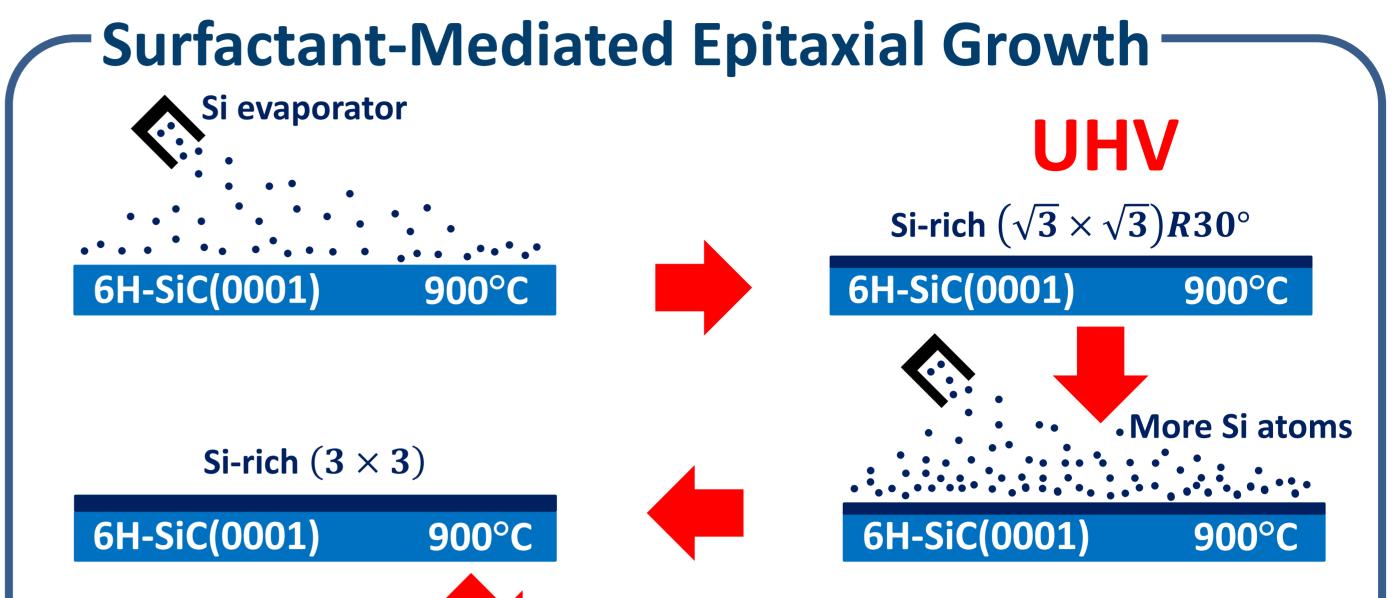
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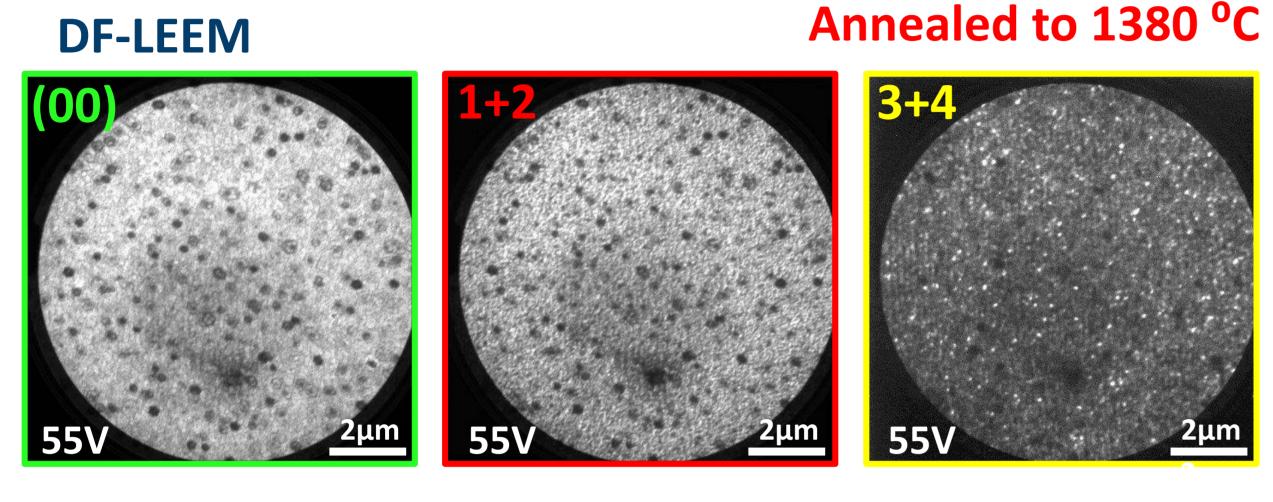
Introduction

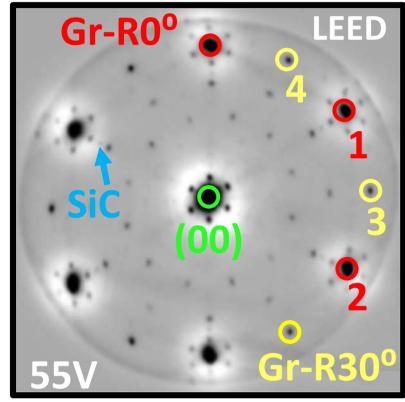
In the exploration of obtaining twisted bilayer graphene (TBG) with a twisting angle of 30°, we investigated the graphene growth on 6H-SiC(0001) using an unconventional epitaxial method named "surfactantmediated growth", which is based on annealing the SiC surface in borazine atmosphere. Here, we report a LEEM-based study on two different samples, on which we observed different surface morphologies with varying number of stacked graphene layers.

[•] Multilayer Graphene R0^o and R30^o









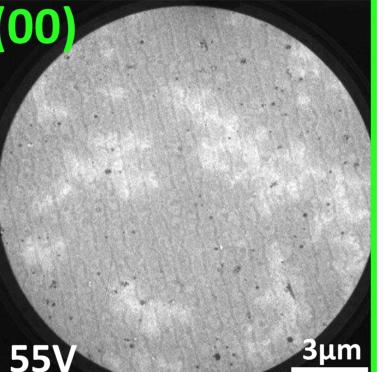
- The surface is much more inhomogeneous than for the 1330°C sample ('(00)' and '1+2');
- Image '(00)' and '1+2' are very similar \rightarrow Gr-R0^o is present (almost) everywhere on the surface;
- Gr-R30^o appears randomly as small bright spots (image '3+4');
- Substrate LEED spots are weaker than for the 1330°C sample \rightarrow Multilayer graphene.

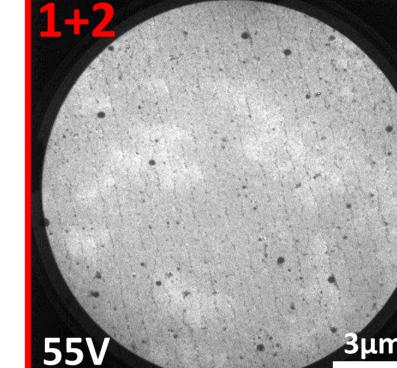
Borazine 1. 5×10^{-6} mbar 6H-SiC(0001) 1330°C/1380°C Multilayer Single-layer **Buffer layer** Gr-R0^o and Gr-R30^o Gr-R0^o $(6\sqrt{3}\times 6\sqrt{3})R30^{\circ}$ 6H-SiC(0001) 6H-SiC(0001) **1380°C 1330°C**

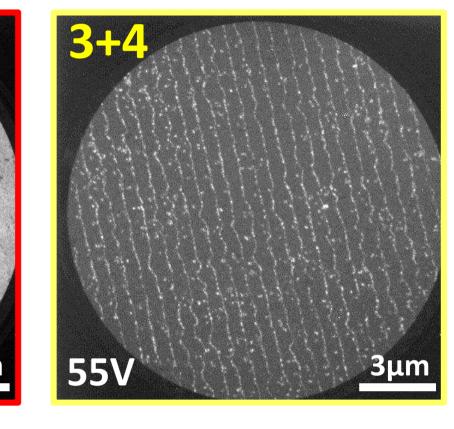
Single-layer Graphene R0°

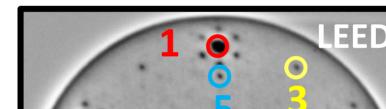
DF-LEEM

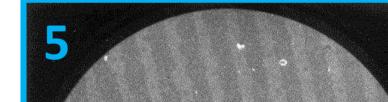
Annealed to 1330 °C

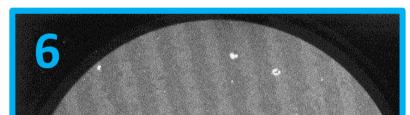




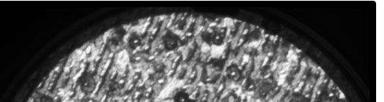


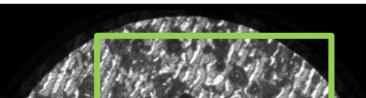


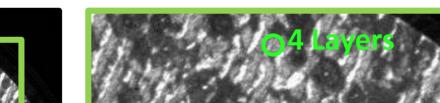


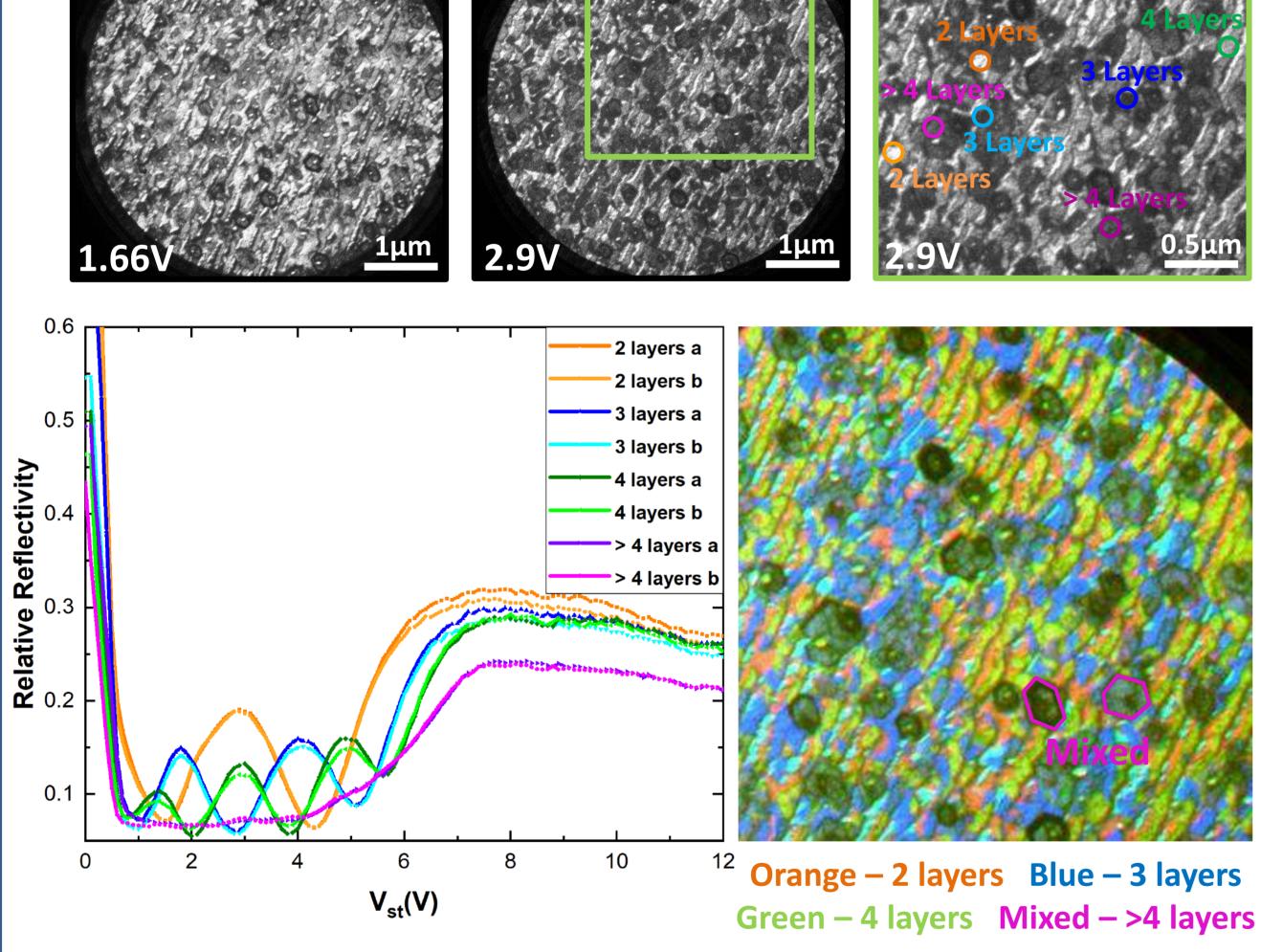


LEEM-IV

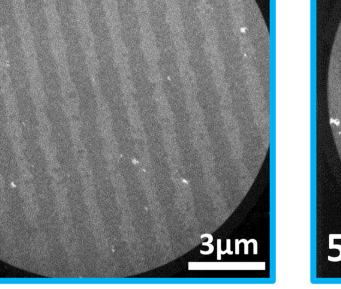


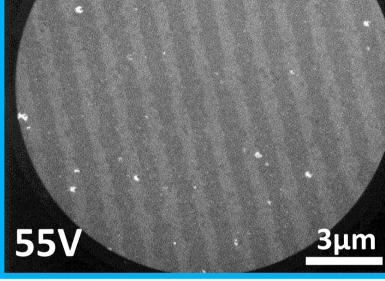






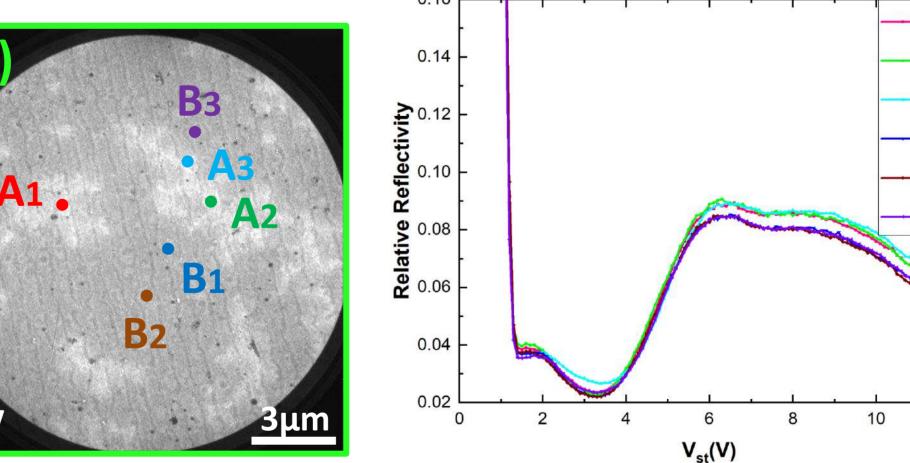
- domains with various number of graphene Small layers, corresponding to the number of minima in the IV curves;
- Domains with 1 to 4 layers clearly identified, and areas with more than 4 layers;





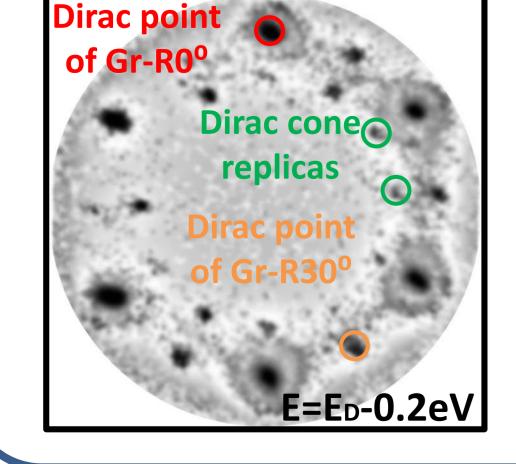
- Uniform Gr-R0^o layer on large scale (> 200µm) (image '1+2');
- Gr-R30^o appears at step edges and a few spots on terraces ('3+4');
- Stripes with alternating brightness in images '5' and '6' reveal the substrate symmetry of 6H-SiC regarding the 60° orientation difference between neighboring terraces.

LEEM-IV



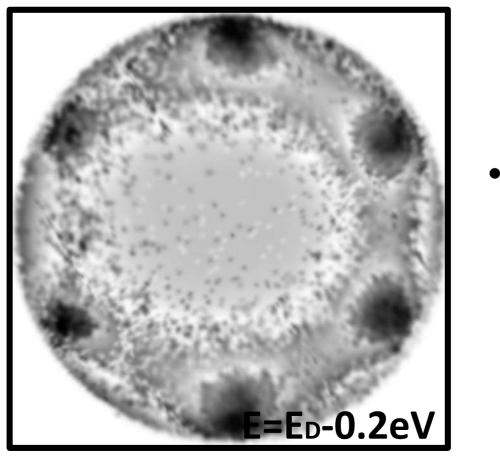
- Only one minimum in the energy range of 0-7V indicates a single graphene layer on the sample surface; Brightness contrast exists at specific start voltages, which could be
- The false color composite image presents the distribution of the different multilayer graphene domains.

ARPES (Constant Energy Map)



- Dirac points of Gr-R0^o and Gr-R30^o can be distinguished, with a much higher intensity for Gr-R0^o. Twelve Dirac cone replicas (in green circles) can be explained by Umklapp-scattering in 30°rotated TBG layers.
- related to a different degree of decoupling from the substrate.

ARPES (Constant Energy Map)



The existence of only six Dirac points illustrates the dominance of the Gr-R0^o layer.

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